

Controlled electronic and magnetic properties of GeAs monolayer by Ge vacancies and doping with transition-metal atoms

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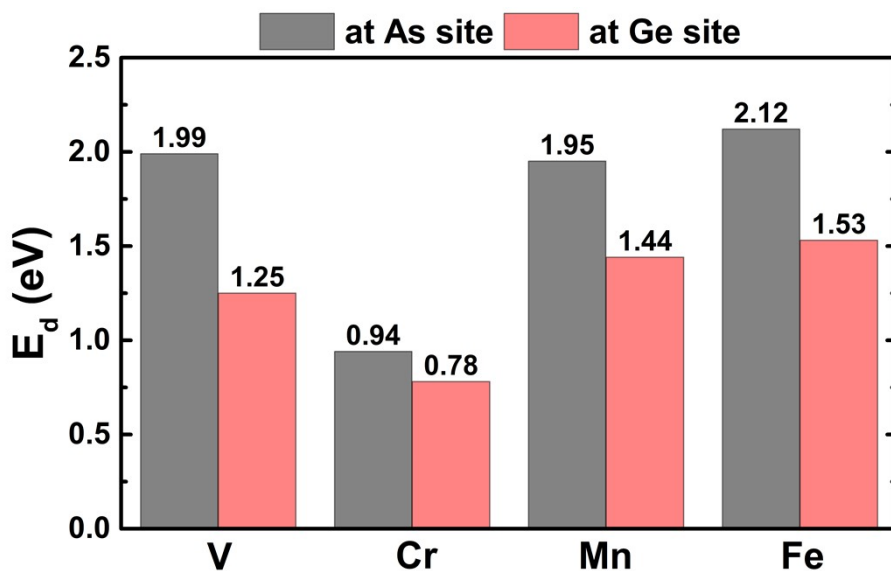


Figure S1: Doping energy of transition metal at Ge and As sites of GeAs monolayer.